

# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										備考	
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>ie</sub> h <sub>ie</sub> * (Ω)	h <sub>re</sub> h <sub>re</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>oe</sub> * (μS)	f <sub>αb</sub> f <sub>r</sub> * (Mc)		C <sub>ob</sub> (pF)
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f<sub>αb</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
- 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)											外形	備考							
				V <sub>CB0</sub> (V)	V <sub>EB0</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>CB0</sub> 最大値		直流又はパルス h <sub>FPE</sub>		バ イ ア ス		h <sub>FE</sub>	h <sub>FE</sub> *	h <sub>FE</sub> *	h <sub>FE</sub> *	f <sub>αβ</sub> *			C <sub>ob</sub>	T <sub>85</sub> h <sub>ic</sub> (real) (Ω)					
									(μA)	V <sub>CB</sub> (V)	V <sub>CE</sub> (V)	I <sub>c</sub> (mA)	V <sub>CB</sub> (V)	I <sub>E</sub> (mA)										h <sub>FE</sub> *	h <sub>FE</sub> *	h <sub>FE</sub> *	(Mc)	(pF)
2SC887	芝 電	SW	Si.TMe	210	5	7 A	50 W (T <sub>c</sub> =25°C)	150	50	30	35	5	1 A												102			
" 888	"	"	"	150	5	7 A	50 W (T <sub>c</sub> =25°C)	150	100	30	35	5	1 A												102			
" 889	三 菱	RF. AF. LN	Si. EP	90	5	7 A	50 W (T <sub>c</sub> =25°C)	150	100	30	35	5	1 A												102			
" 890	日 電	PA	Si. E	40	3	400	750	175	1	20	>20	10	100	10	-50	40									84C			
" 891	"	"	"	40	4	600	10.3W (T <sub>c</sub> =25°C)	175	5	20	>15	10	500	10	-100	40									115			
" 892	"	"	"	40	4	1.2A	17.7W (T <sub>c</sub> =25°C)	175	10	20				10	-300	40									115			
" 893	富士通	RF	Si.TMe	100	6	500	12 W (T <sub>c</sub> =25°C)	175	1	30	100	4	50	4	-50									20*	10	30	97B	
* " 894	ソニー	RF. SW	Si. DB	25	6	100	100	120	0.2	25	100	3	1	6	-2									200*	2.4	C <sub>c</sub> 70pF 120pS	38	
" 895	"	PA. SW	Si.TMe	150	8	2.5 A	23.7 W (T <sub>c</sub> =25°C)	150	50	50	120	3	100	10	-200									20*	145	24	100	
" 896	日 電	RF	Si. E	55	5	200	300	175	1	30				10	-5	70								200*	3.5	35*	46C	
" 897	日 立	PA	Si. T	150	6	7 A	60 W (T <sub>c</sub> =25°C)	150	1mA	30	60	5	1 A	5	-1 A									15*	140		102	2SA757 とコンパ)
" 898	"	"	"	150	5	7 A	80 W (T <sub>c</sub> =25°C)	150	1mA	30	50	5	1 A	5	-1 A									15*	140		102	2SA758 とコンパ)
* " 899	日 電	RF. AF. LN	Si. E	50	5	50	250	125	0.1	15	110	3	0.5	6	-1	140	4000	0.65	8.5					250*	1.8	C <sub>c</sub> 70pF 70pS	138	
" 900	"	RF. LN	"	30	5	30	250	125	0.1	25	400	3	0.5	6	-1									100*	3.5	50*	138	
" 901	松 下	PA	Si.TMe	200	6	5 A	50 W (T <sub>c</sub> =70°C)	150	15mA	150	25	4	5 A	10	-500									50*			102	
" 901A	"	"	Si. EP	250	6	5 A	50 W (T <sub>c</sub> =70°C)	150	15mA	150	25	4	5 A	10	-500									50*			102	
* " 902	富士通	SW	Si.TMe	150	6	10A	75 W (T <sub>c</sub> =25°C)	175	15	30	50	4	5 A														102	
* " 903	三 菱	PA	Si. EP	35	4	300	200	125	1	25	100	2	150	6	-10									150*	10	C <sub>c</sub> 70pF 100pS	138B	
* " 904	"	"	"	50	4	300	200	125	1	25	100	2	150	6	-10									150*	10		138B	
* " 905	"	"	"	65	4	300	200	125	1	25	80	2	150	6	-10									150*	10		138B	
" 906	富士通	PA. SW	"	50	7	500	600	175	0.5	12	160	4	10	6	-1									70*			89	
* " 907	日 立	RF. SW. AF	Si. DB	40	5	100	200	175	0.5	20	200	1	10	6	-1		4000	2	10					240*	1.7	150	12A	
* " 907A	"	"	"	60	5	100	200	175	0.5	20	120	1	10	6	-1		4000	2	10				240*	1.7	150	12A		
" 908	三 菱	PA	Si. EP	40	4	500	860	175	50	15	50	10	100														84B	
* " 909	"	"	"	40	4	500	7 W (T <sub>c</sub> =25°C)	200	50	15	50	10	100														113	
* " 910	"	"	"	40	3	1 A	10 W (T <sub>c</sub> =25°C)	200	100	15				10	-100	50											113	
" 911	"	"	"	40	4	500	1.7W	175	50	15	50	10	100														271	
" 912	"	RF. Conv. Mix Osc. SW	"	30	5	100	150	150	0.1	25	90	6	10	6	-1	80	2500	0.35	15					150*	2.5	C <sub>c</sub> 70pF 100pS	8 A	
" 913	富士通, 日 電	SW	"	40	5	300	300	175	0.2	20	70	1	30														2.5	49C
" 914	"	"	"	40	5	300	300	175	0.2	20	70	1	30														2.5	49C